

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13146	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/706) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 16:01
L2	8	1 and ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 16:01
S1	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 16:01
S2	12	(""4330363") or ("4592799") or ("5021119") or ("5395481") or ("6495405").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:06
S3	2901	((polycrystalline near2 silicon) or (poly adj silicon)) near2 (tft or ((thin near2 film) near2 transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:34
S4	1053	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:19

S5	8	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S6	1	S1 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S7	1152	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:04
S8	4082	S7 and3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S9	12	S7 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S10	1	S9 and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S11	11	S9 not S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:40
S12	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:44

S13	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:54
S14	6	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) near10 (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S15	10	S13 not S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S16	0	("2004/0026738")_URPN	USPAT	OR	OFF	2004/12/08 17:53
S17	123	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S18	107	S17 not S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S19	33	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (crystall\$7 or recrystall\$7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:05
S20	7	S19 and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:07
S21	0	S19 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:08

S22	26	S19 not S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:09
S23	106	((LTPS adj TFT) or (low adj temperature adj polycrystalline adj silicon adj thin adj film adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:21
S24	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 21:21
S25	103	S23 and "1"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26
S26	21	S23 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:22
S27	75	S23 and (amorphous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:30
S28	19	S27 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26

S29	42860	(spc or (solid adj phas adj crystallization)) or (milc or (metal adj induced adj lateral adj crystallization)) or (ela or (excimer adj laser adj annealing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
S30	27	S29 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
S31	0	("2004/0217424").URPN.	USPAT	OR	OFF	2004/12/08 22:38
S32	1	("6242292").PN.	USPAT	OR	OFF	2004/12/08 22:38
S33	52	("3848104" "4046618" "4059461" "4083272" "4160263" "4234358" "4249960" "4266986" "4309225" "4328553" "4341569" "4370175" "4439245" "4463028" "4468551" "4469551" "4545823" "4734550" "4764485" "4803528" "4835704" "4862227" "4937618" "4942058" "4956539" "4970366" "5217921" "5219786" "5221365" "5247375" "5313076" "5352291" "5365875" "5372836" "5413958" "5424230" "5424244" "5432122" "5477073" "5561081" "5572046" "5578520" "5589406" "5612251" "5622814" "5648277" "5696003" "5708252" "5712191" "5736414" "5756364" "5858473").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/08 22:40
S34	20	((("5365080") or ("5847419") or ("6607948") or ("6674100") or ("5063166") or ("4962051") or ("4962051") or ("4914053") or ("4868614"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10
S35	2	("5818053").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10

S36	10741	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 15:38
S37	121	S36 and ((polysilicon near spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:13
S38	0	S36 and ((polysilicon near spacer\$1) near (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
S39	1	S36 and ((polysilicon near spacer\$1) same (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
S40	0	((polysilicon near spacer\$1) near (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
S41	4	((polysilicon near spacer\$1) same (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:55
S42	16	((polysilicon near spacer\$1) and (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:55

S43	0	S36 and ((polysilicon near sidewall near spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
S44	33	S36 and ((polysilicon near sidewall near spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:04
S45	1	S44 and (active adj (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:58
S46	10473	(polysilicon near\$3 spacer\$1) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S47	2040	(polysilicon near\$3 spacer\$1) near (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S48	0	(polysilicon near spacer\$1) near (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S49	34	(polysilicon near spacer\$1) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:10
S50	153	(polysilicon near spacer\$1) and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:10
S51	1	("5589406").PN.	USPAT	OR	OFF	2005/05/13 16:31

S52	395	((ltps adj tft) or ((low near temperature) near transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:34
S53	3	S52 and (polysilicon near2 spacer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:36
S54	46	S52 and (active near (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:41
S55	5	S54 and spacer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:38
S56	5	S54 and ((spacer\$1 or sidewall) same (active near (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:39
S57	1	(soi near mosfet) same (polysilicon near spacer\$1) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:42
S58	4	(soi near mosfet) same (spacer\$1 same (active near2 (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:44
S59	64	(soi near mosfet) same spacer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:44
S60	36	"5589406"	USPAT	OR	OFF	2005/05/16 17:06
S61	1	("5589406").PN.	USPAT	OR	OFF	2005/05/16 17:06

S62	11786	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:44
S63	0	("1and((siliconnear2spacer\$1)near5((activeadj(region\$1orlayer\$1))orchannel\$1)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:45
S64	8	S62 and ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 16:01
S65	1318	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:48
S66	571	(438/487).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:49
S67	1081	(438/166).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:49
S68	977	(438/795).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:49

S69	90	((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:51
S70	6	S69 and (crystalliz\$5 or recrystalliz\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:52